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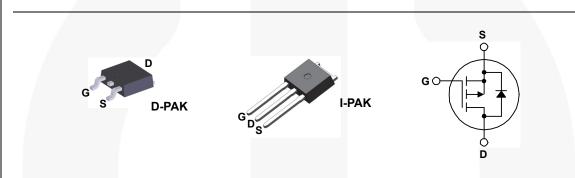
FQD11P06 / FQU11P06 **P-Channel QFET® MOSFET** -60 V, -9.4 A, 185 mΩ

Description

This P-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance • Low Crss (Typ. 45 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, • 100% Avalanche Tested DC motor control, and variable switching power applications...

Features

- -9.4 A, -60 V, R_{DS(on)} = 185 mΩ (Max.) @ V_{GS} = -10 V, I_D = -4.7 A
- Low Gate Charge (Typ. 13 nC)



Absolute Maximum Ratings T_c = 25°C unless otherwise noted.

Symbol	nbol Parameter		FQD11P06TM / FQU11P06TU	Unit	
V _{DSS}	Drain-Source Voltage		-60	V	
I _D	Drain Current - Continuous ($T_C = 25^{\circ}C$)		-9.4	А	
	- Continuous (T _C = 100°C)		-5.95	А	
I _{DM}	Drain Current - Pulsed	(Note 1)	-37.6	А	
V _{GSS}	Gate-Source Voltage	± 30	V		
E _{AS}	Single Pulsed Avalanche Energy		160	mJ	
I _{AR}	Avalanche Current	(Note 1)	-9.4	А	
E _{AR}	Repetitive Avalanche Energy	(Note 1)	3.8	mJ	
dv/dt	Peak Diode Recovery dv/dt (Note		-7.0	V/ns	
P _D	Power Dissipation ($T_A = 25^{\circ}C$) *	2.5	W		
	Power Dissipation ($T_C = 25^{\circ}C$)	38	W		
	- Derate above 25°C	0.3	W/°C		
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C		
TL	Maximum lead temperature for soldering, 1/8" from case for 5 seconds		300	°C	

Thermal Characteristics

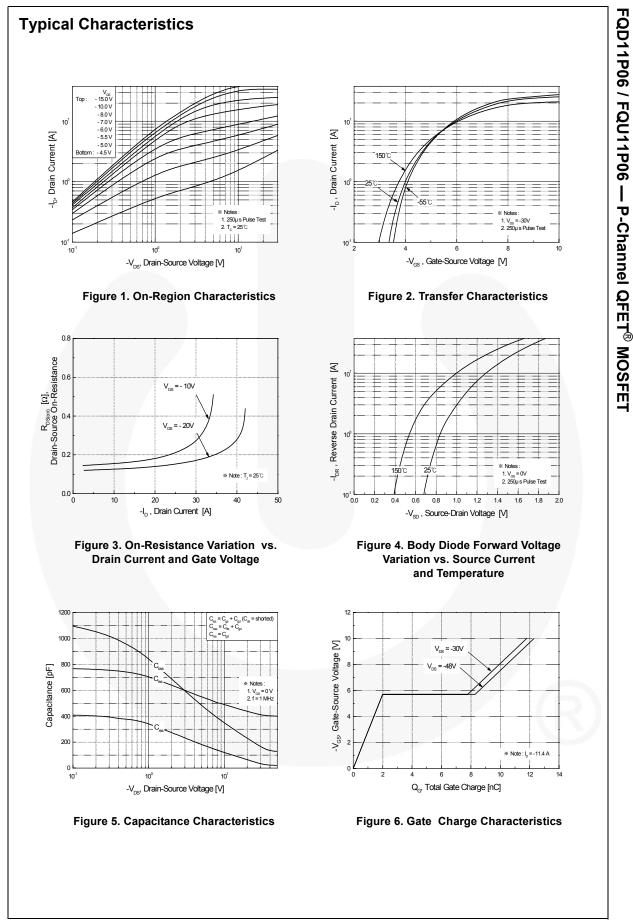
Symbol	Parameter	FQD11P06TM / FQU11P06TU	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	3.28		
D	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	110	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (*1 in ² Pad of 2-oz Copper), Max.	50		

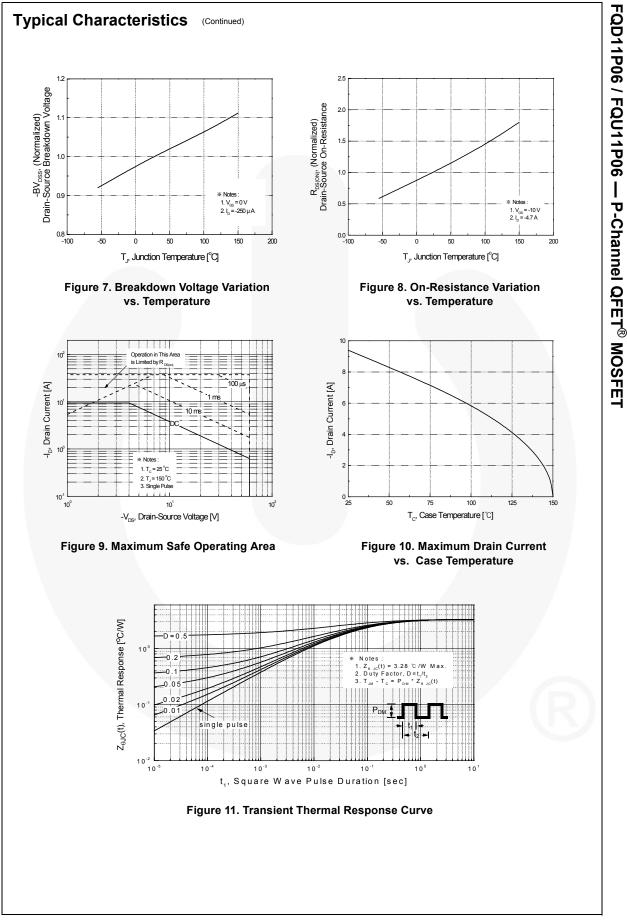
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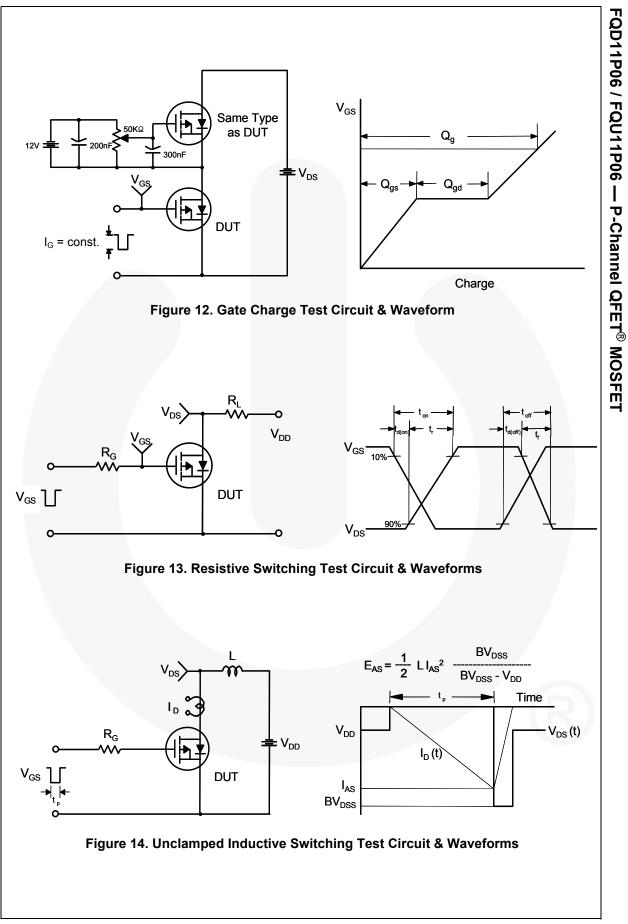
FQD11P06TM FQD11P06		Top Mark	Package		Packing Method Reel		eel Size	Tape W		Quantity 2500 units	
		FQD11P06	D-F	PAK Tape and Reel 33		330 mm	16 m	ım			
		I-P.	PAK Tube N			N/A	N/A		70 units		
lectri	cal Char	acteristics	T _C = 25°	C unless oth	nerwise noted.						
Symbol		Parameter			Test Condition	S	Min	Тур.	Max.	Unit	
Off Cha	racteristi	re internet									
BV _{DSS}	Drain-Source Breakdown Voltage		V _{GS} = 0 V, I _D = -250 μA			-60			V		
ΔBV _{DSS}		Voltage Temperatu	-	$I_D = -250 \ \mu\text{A}$, Referenced to 25°C						-	
$/\Delta T_{J}$	Coefficient	volage temperate					°C	-0.07		V/°C	
I _{DSS}	Zero Gate Voltage Drain Current		V _{DS} = -60 V, V _{GS} = 0 V					-1	μA		
			int	V _{DS} = -48 V, T _C = 125°C					-10	μA	
I _{GSSF}	Gate-Body	Leakage Current, F	orward	V_{GS} = -25 V, V_{DS} = 0 V					-100	nA	
I _{GSSR}	Gate-Body	Leakage Current, F	Reverse	$V_{GS} = 2$	25 V, V _{DS} = 0 V				100	nA	
<u> </u>											
	racteristic		_	N/ 1	/ I = 050 /	`					
V _{GS(th)}		hold Voltage		$V_{DS} = V$	V _{GS} , I _D = -250 μA	4	-2.0		-4.0	V	
R _{DS(on)}	Static Drain On-Resista				-10 V, I _D = -4.7 A			0.15	0.185	Ω	
9 _{FS}	Forward Tra	ansconductance		V _{DS} = -	-30 V, I _D = -4.7 A			4.9		S	
D	a Charact										
-	ic Charact		_	1				420	550	~ F	
C _{iss}	Input Capa		_		25 V, V _{GS} = 0 V,			420	550	pF	
C _{oss}	Output Cap		_	f = 1.0	MHz			195 45	250	pF	
C _{rss}	Reverse II	ansfer Capacitance						45	60	pF	
Switch	ing Chara	cteristics									
t _{d(on)}	Turn-On De		_	V -	201/1 - 57.4			6.5	25	ns	
t _r	Turn-On Ri	se Time	-		V_{DD} = -30 V, I_D = -5.7 A, R _G = 25 Ω			40	90	ns	
t _{d(off)}	Turn-Off De	elay Time		NG - 2	5 22			15	40	ns	
t _f	Turn-Off Fa	II Time				(Note		45	100	ns	
Qg	Total Gate	Charge		V _{DS} = -	-48 V, I _D = -11.4 /	۹,		13	17	nC	
Q _{gs}	Gate-Sourc	e Charge		$V_{GS} = -10 V$ (Note 4)			2.0		nC		
Q _{gd}	Gate-Drain	Charge				e 4)	6.3		nC		
Drain-S	T	de Characteris				js			1	6	
I _S	Maximum Continuous Drain-Source Diode Forward Current					-9.4	A				
I _{SM}		Pulsed Drain-Source							-37.6		
V _{SD}		ce Diode Forward \	/oltage	$V_{GS} = 0 V, I_S = -9.4 A$ $V_{GS} = 0 V, I_S = -11.4 A,$				-4.0	V		
t _{rr}		ecovery Time					83		ns		
Q _{rr}	Reverse Re			dI _F / dt = 100 A/μs				0.26		μC	

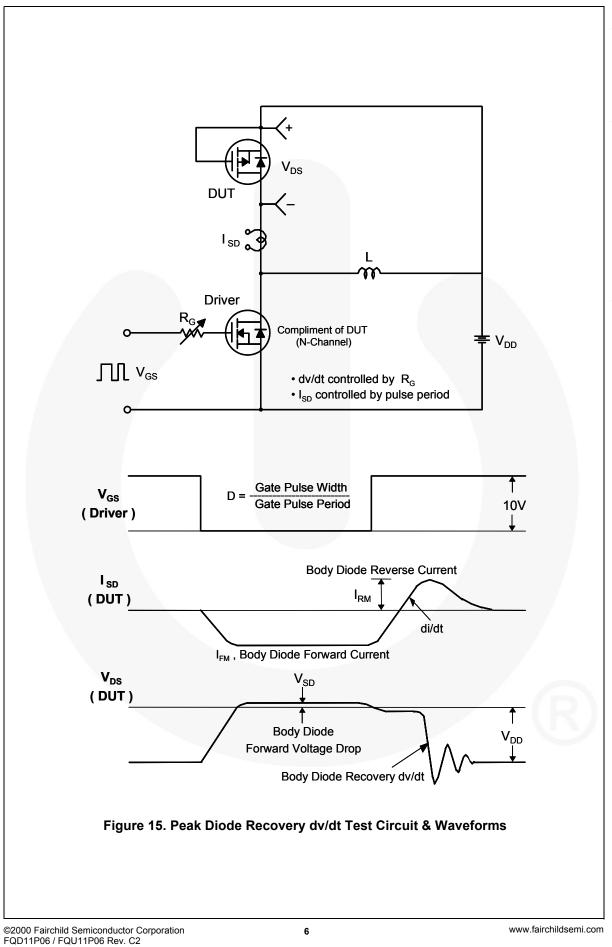
4. Essentially independent of operating temperature.

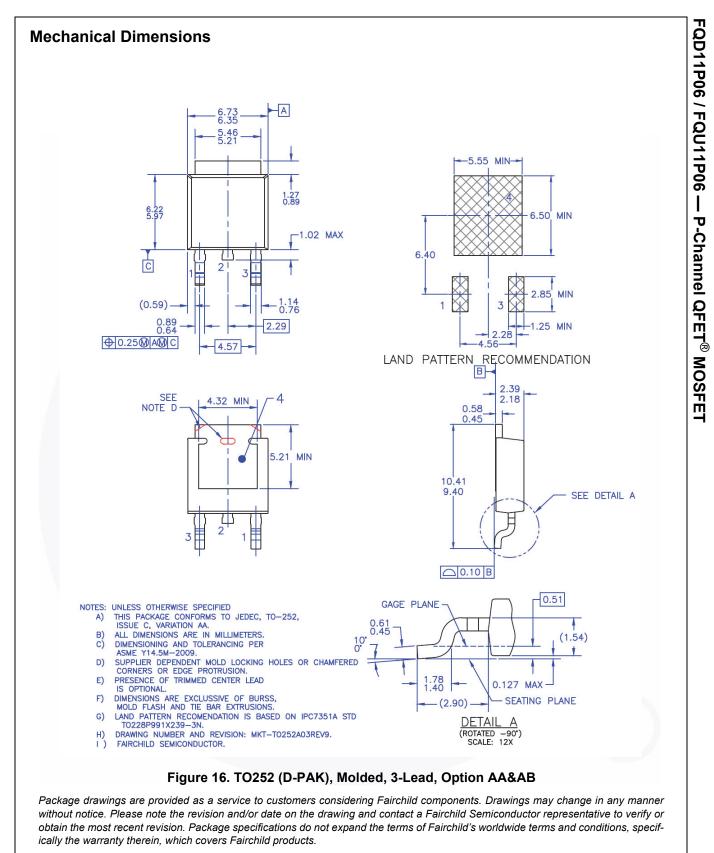
FQD11P06 / FQU11P06 — P-Channel QFET[®] MOSFET





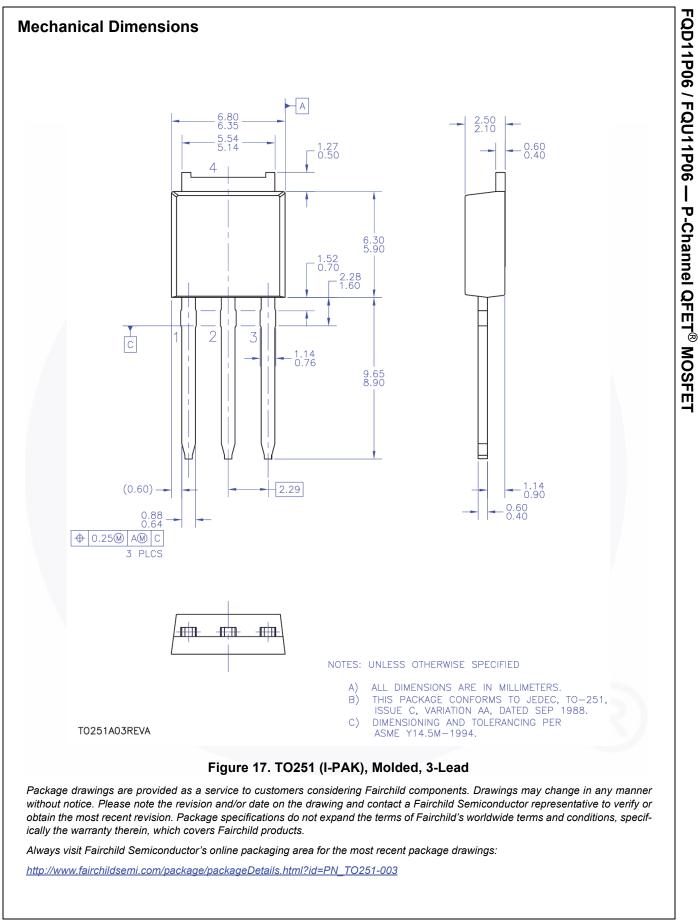






Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT252-003





Obsolete

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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Rev. 166

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